

Linear Systems replaces discontinued Siliconix 2N4117

The 2N4117 is an Ultra-High Input Impedance N-Channel JFET

The 2N4117 provides ultra-high input impedance. The device is specified with a 10-pA limit and is ideal for use as a high-impedance sensitive front-end amplifier.
2N4117 Benefits: <ul style="list-style-type: none"> Insignificant Signal Loss/Error Voltage with High-Impedance Source Low Power Consumption (Battery) Maximum Signal Output, Low Noise High Sensitivity to Low-Level Signals
2N4117 Applications: <ul style="list-style-type: none"> High-Impedance Transducer Smoke Detector Input Infrared Detector Amplifier Precision Test Equipment

FEATURES	
DIRECT REPLACEMENT FOR SILICONIX 2N4117	
LOW POWER	$I_{DSS} < 90 \mu A$
MINIMUM CIRCUIT LOADING	$I_{GSS} < 10 pA$
ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted)	
Maximum Temperatures	
Storage Temperature	-65°C to +175°C
Operating Junction Temperature	-55°C to +150°C
Maximum Power Dissipation	
Continuous Power Dissipation	300mW
MAXIMUM CURRENT	
Gate Current (Note 1)	50mA
MAXIMUM VOLTAGES	
Gate to Drain or Gate to Source (Note 2)	-40V

2N4117 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	-40	--	--	V	$I_G = -1 \mu A, V_{DS} = 0V$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-0.6	--	-1.8	V	$V_{DS} = 10V, I_D = 1nA$
I_{DSS}	Gate to Source Saturation Current	0.03	--	0.09	mA	$V_{DS} = 10V, V_{GS} = 0V$
I_{GSS}	Gate Leakage Current	--	--	-10	pA	$V_{GS} = -20V, V_{DS} = 0V$
g_{fs}	Forward Transconductance(Note 3)	70	--	210	μmho	$V_{GS} = -20V, V_{DS} = 0V, 150^\circ C$
g_{os}	Output Conductance	--	--	3		$V_{DS} = 10V, V_{GS} = 0V, f = 1kHz$
C_{iss}	Input Capacitance	--	--	3	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$
C_{rss}	Reverse Transfer Capacitance	--	--	1.5		

NOTES	1. Absolute maximum ratings are limiting values above which 2N4117 serviceability may be impaired. 2. Due to symmetrical geometry, these units may be operated with source and drain leads interchanged 3. This parameter is measured during a 2ms interval 100ms after power is applied. (Not a JEDEC condition.)
-------	--

Micross Components Europe

Available Packages:

TO-71 (Bottom View)



2N4117 in TO-71
2N4117 in bare die.

Tel: +44 1603 788967
Email: chipcomponents@micross.com
Web: <http://www.micross.com/distribution>

Please contact Micross for full package and die dimensions

